

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1264	(cmos or (complimentary near4 (drain or source or transistor))) and esd and (n-well or nwell or (n near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 14:44
L2	1633	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 15:02
L3	658	257/356.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 17:16
L4	821	257/360.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18
L5	1633	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18
L6	2518	L3 L4 L5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18
L7	1264	(cmos or (complimentary near4 (drain or source or transistor))) and esd and (n-well or nwell or (n near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18
L8	957	L7 and (p near3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18

L9	2205	L6 not L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18
L10	468	L9 and (cmos or complimentary)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:19
L11	473	257/357.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:33
L12	373	11 not 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:33
L13	283	12 not 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:34
L14	658	257/356.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 17:16
L15	538	14 not 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 17:17
L16	357	15 not 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 17:17

L17	339	16 not 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 17:17
S1	1	("6521946").PN.	USPAT	OR	OFF	2005/04/20 16:02
S2	1	("6365932").PN.	USPAT	OR	OFF	2005/04/20 16:02
S3	1	("5543650").PN.	USPAT	OR	OFF	2005/04/20 16:02
S4	3	S1 S2 S3	USPAT	OR	OFF	2005/04/20 16:19
S5	1578	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 15:02
S6	1199	(cmos or (complimentary near4 (drain or source or transistor))) and esd and (n-well or nwell or (n near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:21
S7	907	S6 and (p near3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:36
S8	1	("20050056896").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S9	1	("20050077577").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S10	1	("6855609").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S11	1	("6830966").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S12	1	("6417541").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S13	1	("6835985").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S14	1	("6310380").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:37
S15	7	S8 S9 S10 S11 S12 S13 S14	US-PGPUB; USPAT	OR	OFF	2005/04/20 16:38

S16	646	257/356.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 10:15
S17	802	257/360.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 10:15
S18	1580	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 10:15
S19	2452	S16 S17 S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 10:15
S20	1204	(cmos or (complimentary near4 (drain or source or transistor))) and esd and (n-well or nwell or (n near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 14:32
S21	911	S20 and (p.near3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 10:15
S22	2154	S19 not S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 10:16
S23	454	S22 and (cmos or complimentary)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 16:18